

L Number	Hits	Search Text	DB	Time stamp
1	3	((("6007675") or ("5672239")).PN.	USPAT;	2002/05/28 11:32
-	378708	h011021/\$.ipc. c23c016/\$.ipc.	EPO; JPO	2002/05/23 16:30
-	2107	(h011021/\$.ipc. c23c016/\$.ipc.) and	USPAT;	2002/05/23 16:03
-	1084	(etch\$) and (strip\$3) and (clean\$3)	EPO; JPO	2002/05/23 16:32
-	255	(h011021/\$.ipc. c23c016/\$.ipc.) and	USPAT;	2002/05/23 16:34
-	37	(etch\$) and (strip\$3) and (clean\$3) and	EPO; JPO	2002/05/23 16:37
-	152127	(dry\$3) and ((mov\$3 load\$3 unload\$3	USPAT;	2002/05/23 16:31
-	961	transfer\$3 lift\$3) with (substrate work	EPO; JPO	2002/05/23 16:33
-	403	workpiece object))	USPAT;	2002/05/23 16:37
-	40	((h011021/\$.ipc. c23c016/\$.ipc.) and	EPO; JPO	2002/05/23 16:49
-	363	(etch\$) and (strip\$3) and (clean\$3) and	USPAT;	2002/05/23 17:01
-	55	(dry\$3) and ((mov\$3 load\$3 unload\$3	EPO; JPO	2002/05/23 17:03
-	66	transfer\$3 lift\$3) with (substrate work	USPAT;	2002/05/24 08:49
-	35	workpiece wafer))) and (LCD ("liquid	EPO; JPO	2002/05/24 08:50
-	35	crystal display"))	EPO; JPO	2002/05/24 09:45
-	37511	((438/\$.ccls. 134/\$.ccls. 156/345.\$.	USPAT;	2002/05/24 15:13
-	2473	ccls.) and ((etch\$) and (strip\$3) and	EPO; JPO	2002/05/24 09:55
-	2430	(clean\$3) and (dry\$3) same (substrate	USPAT;	2002/05/24 09:52
-		work workpiece wafer))) and ((mov\$3	EPO; JPO	
-		load\$3 unload\$3 transfer\$3 lift\$3) with	USPAT;	
-		(substrate work workpiece wafer))) not	EPO; JPO	
-		((438/\$.ccls. 134/\$.ccls. 156/345.\$.	USPAT;	
-		ccls.) and ((etch\$) and (strip\$3) and	EPO; JPO	
-		(clean\$3) and (dry\$3) same (substrate	USPAT;	
-		work workpiece wafer))) and ((mov\$3	EPO; JPO	
-		load\$3 unload\$3 transfer\$3 lift\$3) with	USPAT;	
-		(substrate work workpiece wafer))) and	EPO; JPO	
-		(LCD ("liquid crystal display"))	USPAT;	
-		(etch\$3 and strip\$3).ti.	EPO; JPO	
-		156/345.1.ccls.	USPAT;	
-		156/345.2.ccls. not 156/345.1.ccls.	EPO; JPO	
-		156/345.2.ccls.	USPAT;	
-		(etch\$3 and strip\$4) and (semiconductor	EPO; JPO	
-		substrate)	USPAT;	
-		((etch\$3 and strip\$4) and (semiconductor	EPO; JPO	
-		substrate)) and (156/345.\$.	USPAT;	
-		ccls. 216/\$.ccls.)	EPO; JPO	
-		((etch\$3 and strip\$4) and (semiconductor	USPAT;	
-		substrate)) and (156/345.\$.	EPO; JPO	
-		ccls. 216/\$.ccls.)	USPAT;	

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-	1524	((etch\$3 and strip\$4) and (semiconductor substrate)) and (156/345.\$ccls. 451/\$ccls. 216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)	USPAT	2002/05/24 09:58
-	876	((etch\$3 and strip\$4) and (semiconductor substrate)) and (156/345.\$ccls. 451/\$ccls. 216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)) and (elevator vertical convey\$3 transfer\$3)	USPAT	2002/05/24 14:38
-	310	((etch\$3 and strip\$4) and (semiconductor substrate)) and (156/345.\$ccls.))	USPAT	2002/05/24 11:01
-	194	((etch\$3 and strip\$4) and (semiconductor substrate)) and (156/345.\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)	USPAT	2002/05/24 11:02
-	3	"5135608" "5171393" "5376212").PN.	USPAT	2002/05/24 10:29
-	5	5672239.URPN.	USPAT	2002/05/24 10:31
-	2103	((etch\$3 and strip\$4) and (semiconductor substrate)) and (216/\$ccls.))	USPAT	2002/05/24 11:01
-	1312	((etch\$3 and strip\$4) and (semiconductor substrate)) and (216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)	USPAT	2002/05/24 11:02
-	726	((etch\$3 and strip\$4) and (semiconductor substrate)) and (216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)) and (elevator vertical convey\$3 transfer\$3)	USPAT	2002/05/24 11:03
-	412	((etch\$3 and strip\$4) and (semiconductor substrate)) and (216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)) and (elevator vertical)	USPAT	2002/05/24 11:15
-	374	((etch\$3 and strip\$4) and (semiconductor substrate)) and (216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)) and (elevator vertical)) not (((etch\$3 and strip\$4) and (semiconductor substrate)) and (156/345.\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3))	USPAT	2002/05/24 14:29
-	2	6074946.URPN.	USPAT	2002/05/24 11:58
-	1	"5369053".PN.	USPAT	2002/05/24 11:59
-	1	((etch\$3 and strip\$4) and (semiconductor substrate)) and (451/\$ccls.) and elevator	USPAT	2002/05/24 14:23
-	154	((etch\$3 and strip\$4) and (semiconductor substrate)) and (451/\$ccls.))	USPAT	2002/05/24 14:29
-	147	((etch\$3 and strip\$4) and (semiconductor substrate)) and (451/\$ccls.)) not (((etch\$3 and strip\$4) and (semiconductor substrate)) and (216/\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3)) and (elevator vertical)) not (((etch\$3 and strip\$4) and (semiconductor substrate)) and (156/345.\$ccls.)) and (wash\$3 rins\$3 clean\$3 dip\$3))	USPAT	2002/05/24 14:30
-	5849	(etch\$3 and strip\$4) and (semiconductor substrate)	EPO; JPO; DERWENT	2002/05/24 14:39
-	2232	((etch\$3 and strip\$4) and (semiconductor substrate)) and (h011021/\$ipc. c23c016/\$ipc.)	EPO; JPO; DERWENT	2002/05/24 14:42
-	18	((etch\$3 and strip\$4) and (semiconductor substrate)) and (h011021/\$ipc. and c23c016/\$ipc.)	EPO; JPO; DERWENT	2002/05/24 14:44
-	192	((etch\$3 and strip\$4) and (semiconductor substrate)) and (h011021/\$ipc. c23c016/\$ipc.)) and (wash\$3 rins\$3 clean\$3 dip\$3)	EPO; JPO; DERWENT	2002/05/24 14:46
-	5	(etch\$3 and strip\$4) and (semiconductor substrate) and (strip\$4 with elevator)	USPAT; EPO; JPO	2002/05/24 15:16
-	133	(etch\$3 and strip\$4) and (semiconductor substrate) and elevator	USPAT; EPO; JPO	2002/05/24 15:27